

N-Channel MOSFETs (>500V...900V); Package: PG-TO220-3; VDS (max): 800.0 V; RDS(ON) @ TJ=25°C VGS=10: 450.0 mOhm; ID(max) @ TC=25°C: 11.0 A; IDpuls (max): 33.0 A; MOSFET COOL MOS N-CH 800V 11A



Images are for reference only

Manufacturers	<a href="#">Infineon Technologies Corporation</a>
Package/Case	TO-220F
Product Type	Transistors
RoHS	
Lifecycle	

Please submit RFQ for SPP11N80C3 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

SPP11N80C3 is a specific model of power MOSFET (metal-oxide-semiconductor field-effect transistor) manufactured by Infineon Technologies AG.

### Features

It has a voltage rating of 800V and can handle a current of 11A.

The device is designed to offer low on-state resistance and fast switching characteristics, which makes it suitable for high-efficiency power conversion applications.

The MOSFET also features a built-in body diode, which makes it useful in flyback and synchronous rectification circuits.

### Application

Due to its high voltage and current rating, the SPP11N80C3 is widely used in power supply applications, including switched-mode power supplies (SMPS) and DC-DC converters.

It can also be used in motor control circuits and lighting applications.



### Related Products



#### [BSP613P](#)

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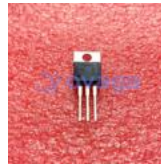
#### [SPP11N65C3](#)

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TO-220



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[SPP07N60S5](#)

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